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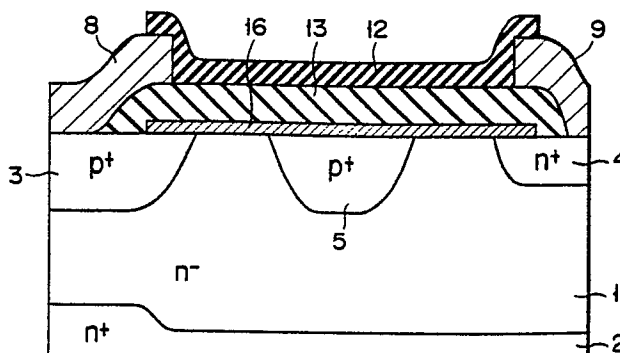
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Semiconductor device with a high breakdown voltage.

There is disclosed a power transistor comprising a semiconductor substrate (1) having a PN junction exposed on a major surface of the semiconductor substrate, and a semiinsulative polysilicon film (16) formed on the major surface, the polysilicon film covering the PN junction, the polysilicon film containing at least one of carbon, oxygen, and nitrogen, and the polysilicon film having a thickness of about 3,000 Å.

FIG. 5





DOCUMENTS CONSIDERED TO BE RELEVANT			
Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int. Cl.4)
X	JAPANESE JOURNAL OF APPLIED PHYSICS, vol. 15, no. 7, 1976, supplement, pages 41-48, Tokyo, JP; H. MOCHIZUKI et al.: "Semi-insulating polycrystalline-silicon (SIPOS) films applied to MOS integrated circuits" * Page 44, right-hand column, line 18 - page 45, left-hand column, line 21; figure 7 *	1	H 01 L 29/06
A	Idem	2-4	
A	--- US-A-3 971 061 (MATSUSHITA et al.) * Abstract; figure 7 *	1-4	
A	--- GB-A-2 047 461 (PHILIPS) * Abstract; page 2, line 99 - page 3, line 8; figures 2,4 *	1-5	TECHNICAL FIELDS SEARCHED (Int. Cl.4) H 01 L
D,A	--- IEEE TRANSACTIONS ON ELECTRON DEVICES, vol. ED-23, no. 8, August 1976, pages 826-830, IEEE, New York, US; T. MATSUSHITA et al.: "Highly reliable high-voltage transistors by use of the SIPOS process" * Whole document *	1-5	
The present search report has been drawn up for all claims			
Place of search THE HAGUE		Date of completion of the search 17-09-1987	Examiner BAILLET B.J.R.
CATEGORY OF CITED DOCUMENTS X : particularly relevant if taken alone Y : particularly relevant if combined with another document of the same category A : technological background O : non-written disclosure P : intermediate document T : theory or principle underlying the invention E : earlier patent document, but published on, or after the filing date D : document cited in the application L : document cited for other reasons & : member of the same patent family, corresponding document			